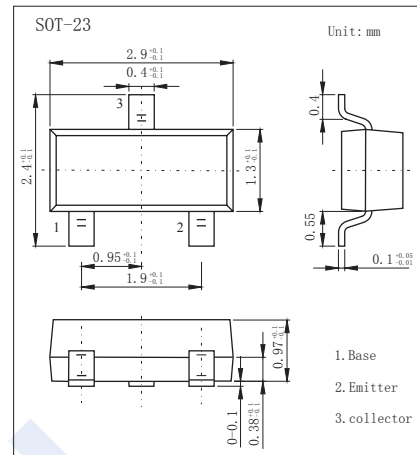


PNP Transistors

2SA1464

■ Features

- High f_T : $f_T = 400\text{MHz}$
- Complementary to 2SC3739



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-60	V
Collector - Emitter Voltage	V _{CE0}	-40	
Emitter - Base Voltage	V _{EB0}	-5	
Collector Current - Continuous	I _C	-500	mA
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = -100 μA, I _E =0	-60			V
Collector- emitter breakdown voltage	V _{CE0}	I _C = -1 mA, I _B =0	-40			
Emitter - base breakdown voltage	V _{EB0}	I _E = -100 μ A, I _C =0	-5			
Collector-base cut-off current	I _{CBO}	V _{CB} = -40 V , I _E =0			-0.1	uA
Emitter cut-off current	I _{EBO}	V _{EB} = -4V , I _C =0			-0.1	
Collector-emitter saturation voltage *	V _{CE(sat)}	I _C =-500 mA, I _B =-50 mA		-0.45	-0.75	V
Base - emitter saturation voltage *	V _{BE(sat)}	I _C =-500 mA, I _B =-50 mA		-1	-1.3	
DC current gain *	h _{FE(1)}	V _{CE} = -2V, I _C = -150mA	75	140	300	
	h _{FE(2)}	V _{CE} =- 2V, I _C = -500mA	20	50		
Turn-on time	t _{on}	V _{CC} =-30V I _C = -150mA, I _{B1} =-I _{B2} = -15mA			35	ns
Storage time	t _{stg}				225	
Turn -off time	t _{off}				255	
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0,f=1MHz		5	8	pF
Transition frequency	f _r	V _{CE} = -10V, I _E = 20mA	150	400		MHz

* : Pulsed:PW $\leq$ 350us,Duty Cycle $\leq$ 2%

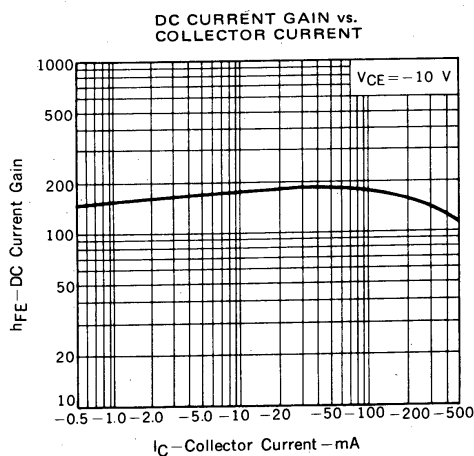
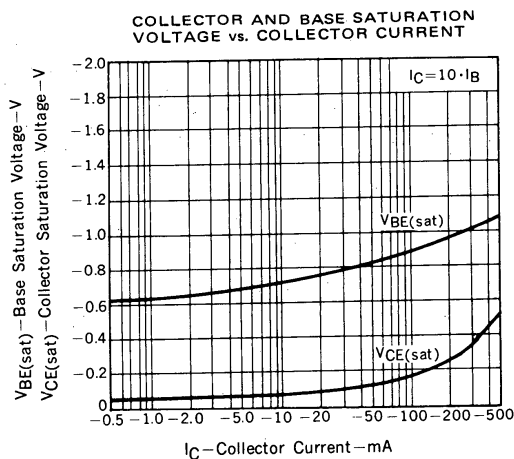
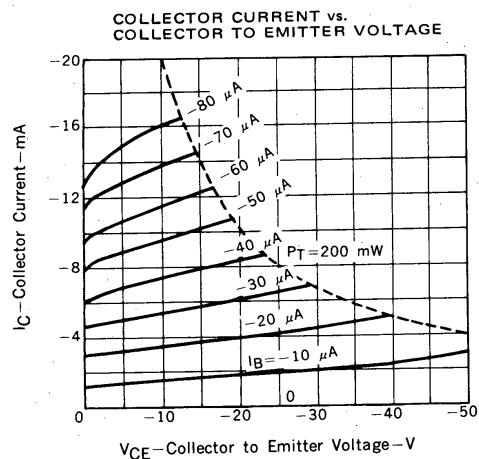
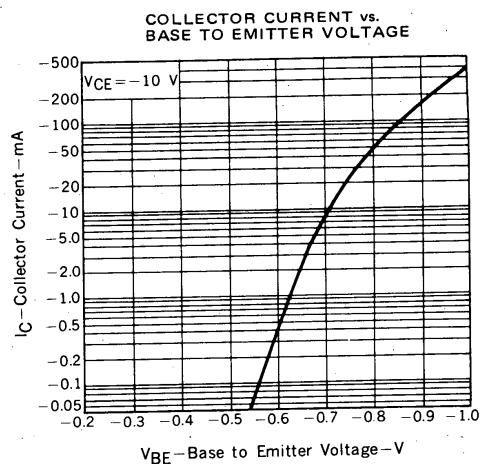
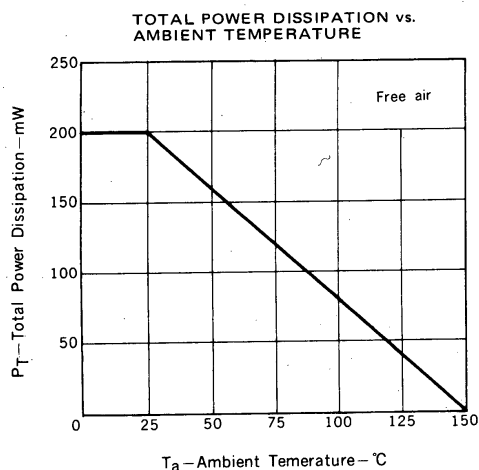
■ Classification of $\text{hfe}(1)$

Type	2SA1464-Y12	2SA1464-Y13	2SA1464-Y14
Range	75-150	100-200	150-300
Marking	Y12	Y13	Y14

PNP Transistors

2SA1464

■ Typical Characteristics



PNP Transistors

2SA1464

■ Typical Characteristics

